



Response Under 37 CFR § 1.116
Expedited Procedure

501.42841X00

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IPW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): KUMAGAI, et al.
Serial No.: 10/625,616
Filed: July 24, 2003
For: SEMICONDUCTOR DEVICE INCLUDING N-CHANNELED
FETs AND P-CHANNELED FETs WITH IMPROVED DRAIN
CURRENT CHARACTERISTICS (*As Amended*)
Group: 2811 Exr. H. Vu

AMENDMENT AFTER FINAL

MS: AFTER FINAL

Commissioner of Patents
POB 1450
Alexandria, VA 22313-1450

Jan. 18, 2006

Sir:

In response to the Final Office Action dated October 18, 2005, please amend the above-identified application as listed below and as set forth on the following pages:

Amendments to the Claims; and

Remarks are included following the amendments.